

FDS6694-VB Datasheet

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A) ^a	Q _g (Typ.)			
30	0.008 at V _{GS} = 10 V	13	6.1 nC			
	0.011 at V _{GS} = 4.5 V	11	0.1110			

SO-8

Top View

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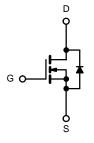
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FEATURES

- · Halogen-free
- Trench Power MOSFET
- Optimized for High-Side Synchronous Rectifier Operation
- 100 % R_g Tested
- 100 % UIS Tested

APPLICATIONS

- Notebook CPU Core
 - High-Side Switch



N-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage	V_{GS}	± 20	v		
	T _C = 25 °C		13		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	I_	10		
Continuous Drain Current (1) = 130 C)	T _A = 25 °C	I _D	9 ^{b, c}		
	T _A = 70 °C		7 ^{b, c}		
Pulsed Drain Current	I _{DM}	45	A .		
Continuous Source-Drain Diode Current	T _C = 25 °C	I.	3.7		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	2.0 ^{b, c}		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20		
Avalanche Energy	L = 0.111111	E _{AS}	21	mJ	
	T _C = 25 °C		4.1		
Maximum Dawar Dissination	T _C = 70 °C	P _D	2.5	□ w	
Maximum Power Dissipation	$T_A = 25 ^{\circ}\text{C}$		2.2 ^{b, c}	vv	
	T _A = 70 °C		1.3 ^{b, c}	7	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	39	55	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	25	29	C/vv	

Notes:

- a. Base on $T_C = 25$ °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under Steady State conditions is 85 °C/W.



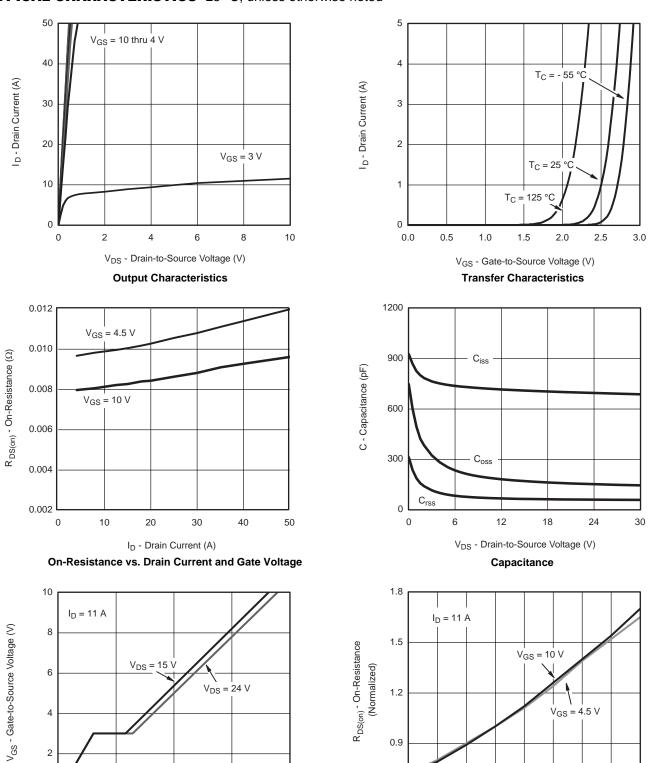
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	1					
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$	30			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 250A		26		mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	I _D = 250 μA		- 6		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		3.0	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		V _{DS} = 30 V, V _{GS} = 0 V			1	μΑ
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α
	_	V _{GS} = 10 V, I _D = 10 A		0.008		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 9 A	0.000			Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		50		S
Dynamic ^b						
Input Capacitance	C _{iss}			800		pF
Output Capacitance	C _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		165		
Reverse Transfer Capacitance	C _{rss}			73		
Total Gate Charge		V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A		15	23	23 10.2 nC
	Q _g	20 00 2		6.8	10.2	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 10 \text{ A}$		2.5		
Gate-Drain Charge	Q _{gd}			2.3		
Gate Resistance	R _g	f = 1 MHz	0.36	1.8	3.6	Ω
Turn-On Delay Time	t _{d(on)}			16	23	
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_{L} = 1.4 \Omega$		12	16	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 9 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		16	22	1
Fall Time	t _f			10	18	1
Turn-On Delay Time	t _{d(on)}			8	16	ns
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_{L} = 1.4 \Omega$		10	20	- - -
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 9 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		16	22	
Fall Time	t _f			8	15	
Drain-Source Body Diode Characterist	tics			1	'	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			10	۸
Pulse Diode Forward Current ^a	I _{SM}				50	- A
Body Diode Voltage	V _{SD}	I _S = 9 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			15	30	ns
Body Diode Reverse Recovery Charge	Q _{rr}	L 0.4 dl/dt 100.4/vs T 25.00		6	12	nC
Reverse Recovery Fall Time	t _a	I _F = 9 A, dl/dt = 100 A/μs, T _J = 25 °C		8		
Reverse Recovery Rise Time	t _b			7		ns

Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





0.6

- 50

- 25

0

25

50

T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature

75

100

125

150

16

服务热线:400-655-8788

0

0

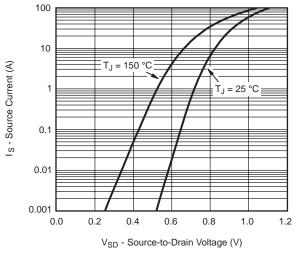
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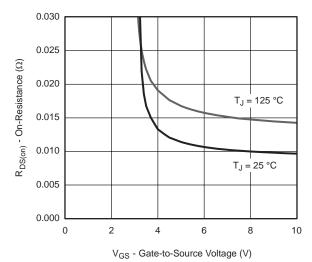
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Q_q - Total Gate Charge (nC)

Gate Charge

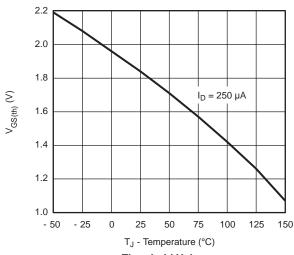


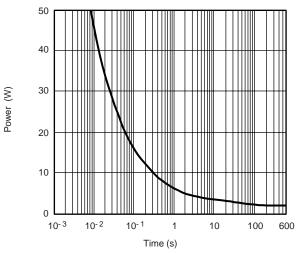




Source-Drain Diode Forward Voltage

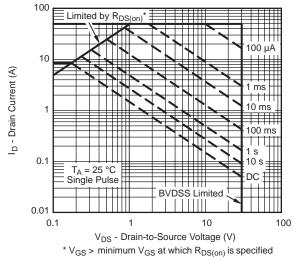






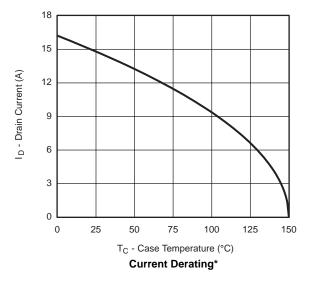
Threshold Voltage

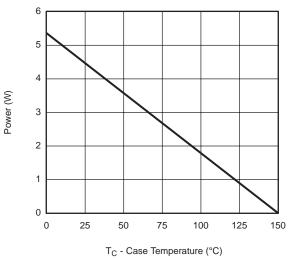
Single Pulse Power, Junction-to-Ambient

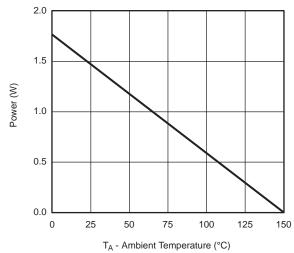


Safe Operating Area, Junction-to-Ambient







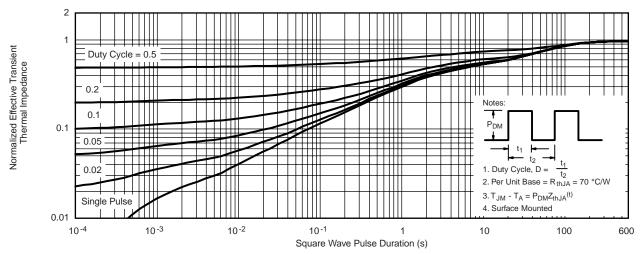


Power Derating, Junction-to-Foot

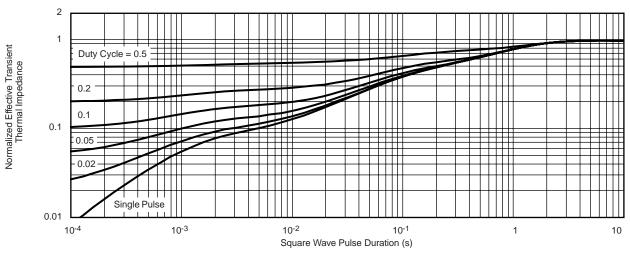
Power Derating, Junction-to-Ambient

^{*} The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





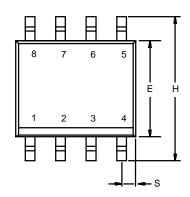
Normalized Thermal Transient Impedance, Junction-to-Ambient

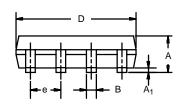


Normalized Thermal Transient Impedance, Junction-to-Foot



SOIC (NARROW): 8-LEAD







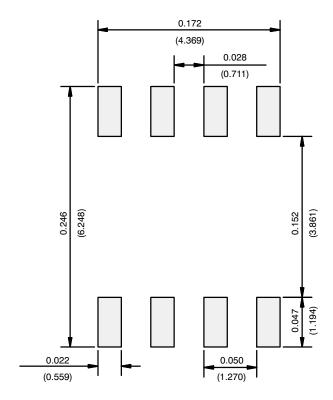
	MILLIMETERS		INC	HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27 BSC		0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
FCN: C-06527-Rev 11-Sen-06						

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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